Amendments to the Claims:

1. (Previously Presented) A chip for a chip-containing portable article comprising:

   a silicon substrate layer having an active face with circuits integrated therein defining a central processor unit and memories; and

   an additional layer of silicon that:

   is sealed to the active face of the silicon substrate layer by a sealing layer;

   covers at least part of said active face; and

   comprises physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm.

2. (Withdrawn)

3. (Withdrawn)

4. (Cancelled)

5. (Previously Presented) A chip according to Claim 1, wherein the physical means for providing physical protection against the action of electromagnetic radiation are silicon dopants.

6. (Previously Presented) A chip according to Claim 5, wherein the concentration of silicon dopants lies in the range 10^{17} to 10^{20} atoms per cm^3.

7. (Previously Presented) A chip according to Claim 5, wherein the silicon dopants are phosphorus or boron.

8. (Cancelled)

9. (Cancelled)

10. (Previously Presented) A chip according to Claim 1, wherein the physical means for providing physical protection against the action of electromagnetic radiation are formed by surface irregularities.

11. (Cancelled)

12. (Previously Presented) A chip according to claim 10, wherein the surfaces irregularities are provided in the face of the additional layer of silicon that is in contact with the sealing layer.

13. (Previously Presented) A chip according to Claim 10, wherein the surface irregularities are provided in the face of the additional layer of silicon that is opposite to the face that is in contact with the sealing layer.

14. (Previously Presented) A chip according to Claim 1, wherein the physical means for providing physical protection against the action of electromagnetic radiation are formed by at least one deposition of metal on the additional layer of silicon.

15. (Previously Presented) A chip according to Claim 14, wherein the metal deposition has a thickness greater than 50 Å.

16. (Previously Presented) A chip according to Claim 14, wherein the metal deposition is on the face of the additional of silicon that is in contact with the sealing layer.

17. (Previously Presented) A chip according to Claim 14, wherein the metal deposition is on the face of the additional layer of silicon that is opposite to the face that is in contact with the sealing layer.

18. (Cancelled)

19. (Previously Presented) A chip according to claim 16, wherein the metal deposition has a thickness of about 100 Å.

20. (Previously Presented) A portable article provided with a chip comprising: a silicon substrate layer having an active face with circuits integrated therein defining a central processor unit and memories; and

an additional layer of silicon that:

is sealed to the active face of the silicon substrate layer by a sealing layer;

covers at least part of said active face; and

comprises physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm.

21. (Previously Presented) The chip according to Claim 5 wherein the silicon substrate layer comprises:

physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm; and

wherein said physical means comprises silicon dopants in the face of the silicon substrate layer that is opposite to the active face.

22. (Previously Presented) The chip according to Claim 21, wherein the concentration of silicon dopants in the silicon substrate layer lies in the range 10^{17} to 10^{20} atoms per cm^3.

23. (Previously Presented) The chip according to Claim 22, wherein the silicon dopants in the silicon substrate layer are phosphorus or boron.

23. (Previously Presented) A chip according to Claim 10 wherein the silicon substrate layer comprises:

physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm: and

wherein said physical means comprises surface irregularities in the face of the silicon substrate layer that is opposite to the active face.

24. (Previously Presented) A chip according to Claim 14 wherein the silicon substrate layer comprises:

physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm; and

wherein said physical means comprising deposition of metal on the face of the silicon substrate layer that is opposite to the active face.

25. (Previously Presented) A chip for a chip-containing portable article comprising:

a silicon substrate layer having an active face with circuits integrated therein defining a central processor unit and memories; and

physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm comprising silicon dopants in the face of the silicon substrate layer that is opposite to the active face.

26. (Previously Presented) A chip according to Claim 25, wherein the concentration of silicon dopants lies in the range 10^{17} to 10^{20} atoms per cm^3.

27. (New) A chip according to Claim 26, wherein the silicon dopants are phosphorus or boron.

28. (Previously Presented) A chip for a chip-containing portable article comprising:

a silicon substrate layer having an active face with circuits integrated therein defining a central processor unit and memories; and

physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm comprising surface irregularities in the face of the silicon substrate layer that is opposite to the active face.

29. (Previously Presented) A chip for a chip-containing portable article comprising:

a silicon substrate layer having an active face with circuits integrated therein defining a central processor unit and memories; and

physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm comprising deposition of metal on the face of the silicon substrate layer that is opposite to the active face.

30. (Previously Presented) A chip according to Claim 29, wherein the metal deposition has a thickness greater than 50 Å.

31. (Previously Presented) A chip according to claim 29, wherein the metal deposition has a thickness of about 100 Å.